

ESD Protection Diodes with Ultra-Low Capacitance

1-Line, Bi-directional, Transient Voltage Suppressors

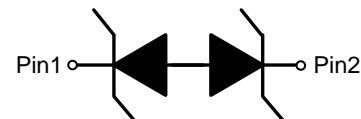
Descriptions

The ESD5D003SA is a bi-directional TVS (Transient Voltage Suppressor). It is specifically designed to protect sensitive electronic components that may be subjected to ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning. It is particularly well-suited for cellular phones, portable device, digital cameras, power supplies and many other portable applications because of its small package and low weight.



DFN1006-2L

The ESD5D003SA may be used to provide ESD protection up to $\pm 20\text{KV}$ Air, $\pm 15\text{KV}$ contact compliance to IEC61000-4-2, and withstand peak pulse current up to 4 A (8/20 μs) according to IEC61000-4-5.



Circuit diagram

The ESD5D003SA is available in DFN1006-2L package. Standard products are Pb-free and Halogen-free.

Features

- Stand-off voltage: $\pm 5\text{V}$ Max
- Transient protection for each line according to IEC61000-4-2 (ESD): $\pm 20\text{KV}$ Air, $\pm 15\text{KV}$ contact
- IEC61000-4-5 (Surge): 4 A (8/20 μs)
- Solid-state silicon technology
- Low leakage current

Order information

Device	Marking	Package	Shipping
ESD5D003SA	5U	DFN1006-2L	10000/Tape&Reel

Applications

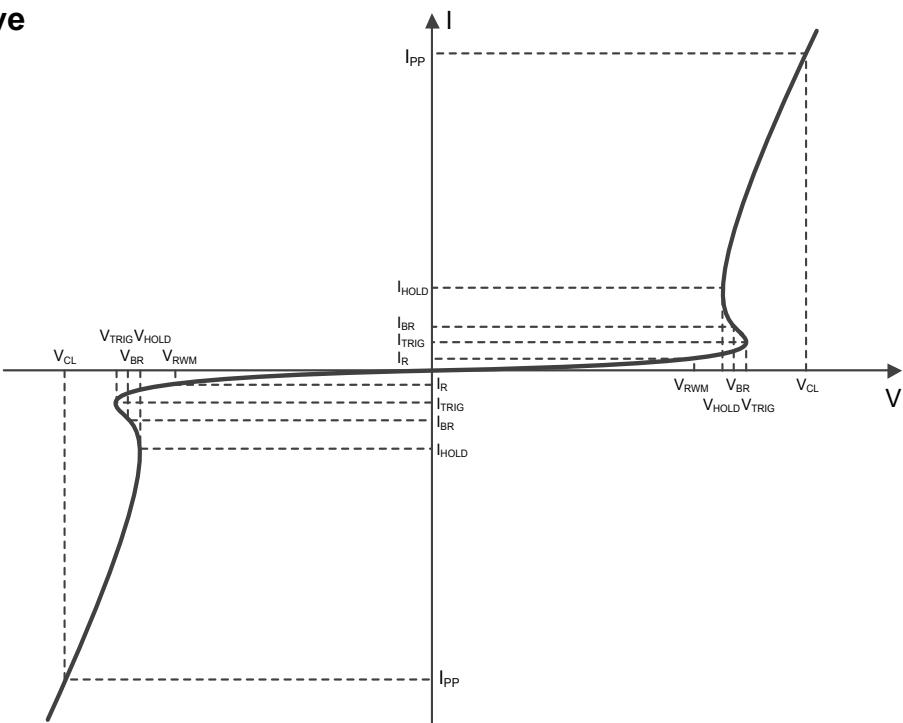
- Cell phone handsets and accessories
- Personal Digital Assistants (PDAs)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Digital Cameras
- CAR/MID DVD/MP3/MP4/PMP Players

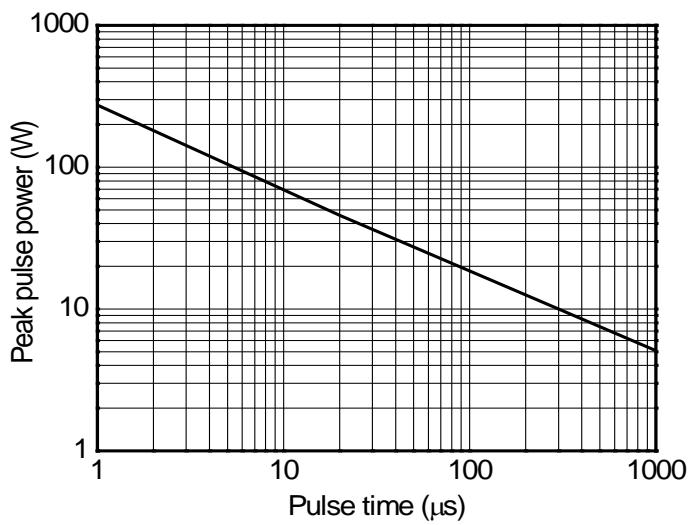
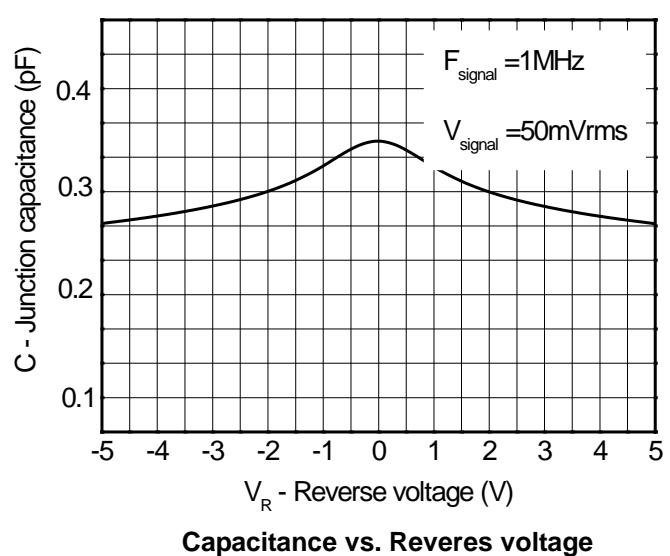
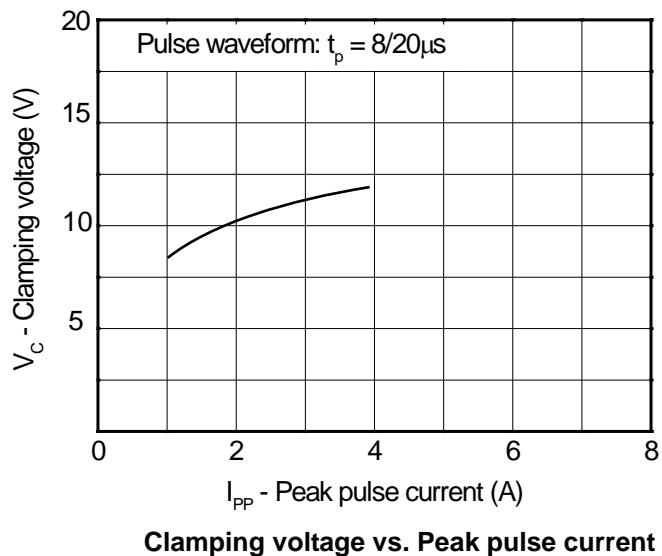
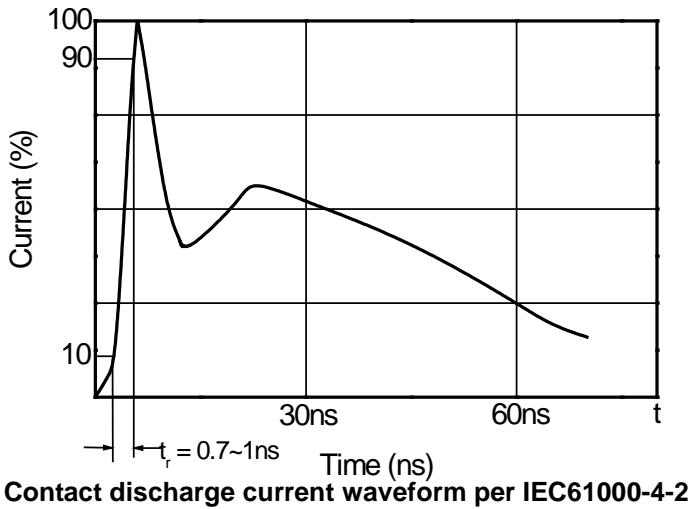
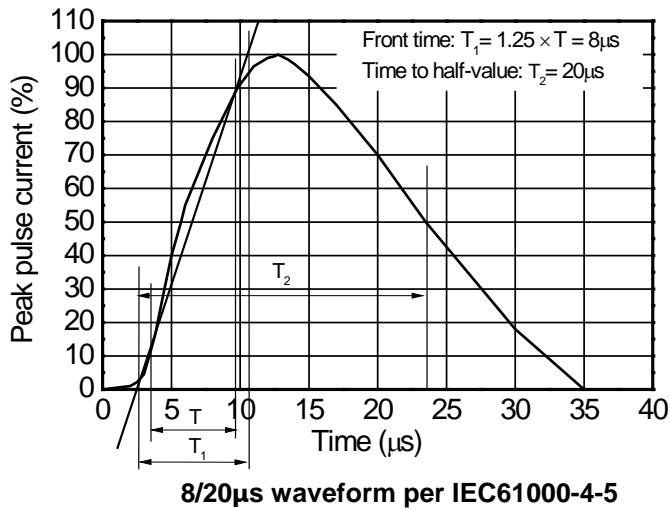
Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	4	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 20	kV
ESD according to IEC61000-4-2 contact discharge		± 15	
Operating temperature	T_{OP}	-40~85	$^{\circ}C$
Operation junction temperature	T_J	125	$^{\circ}C$
Lead temperature	T_L	260	$^{\circ}C$
Storage temperature	T_{STG}	-55~150	$^{\circ}C$

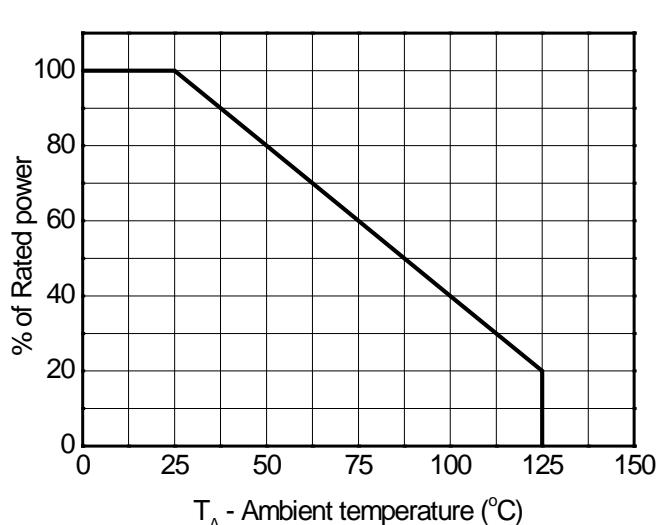
Electrical characteristics (TA=25 °C ,unless otherwise noted)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				± 5	V
Reverse leakage current	I_R	$V_{RWM} = 5V$			100	nA
Reveres breakdown voltage	V_{BR}	$I_T=1mA$	6.5	8.5		V
Clamping voltage	V_C	$I_{PP}=1A$ tp=8/20us		9.3	10	V
Clamping voltage	V_C	$I_{PP}=4A$ tp=8/20us			12	V
Junction capacitance	C_J	$V_R = 0V$, f = 1MHz		0.4	0.6	pF

Electrical performance curve V_{RWM} Reverse stand-off voltage I_R Reverse leakage current V_{CL} Clamping voltage I_{PP} Peak pulse current V_{TRIG} Reverse trigger voltage I_{TRIG} Reverse trigger current V_{BR} Reverse breakdown voltage I_{BR} Reverse breakdown current V_{HOLD} Reverse holding voltage I_{HOLD} Reverse holding current

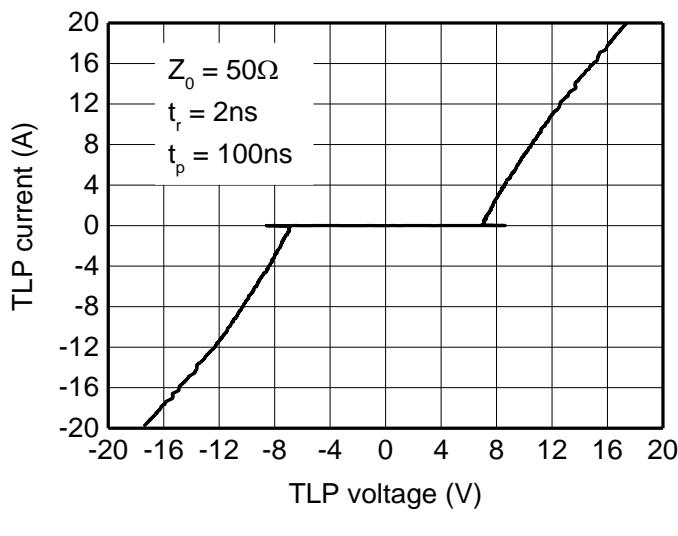
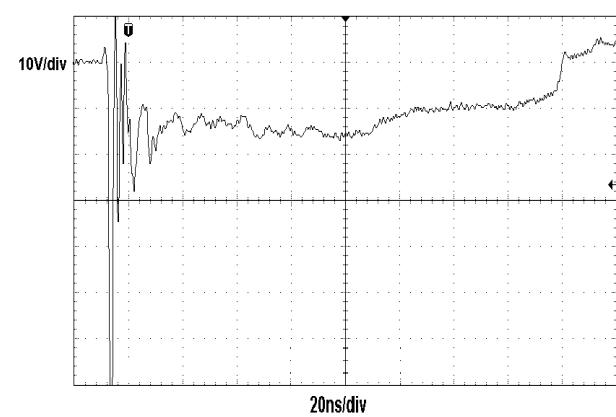
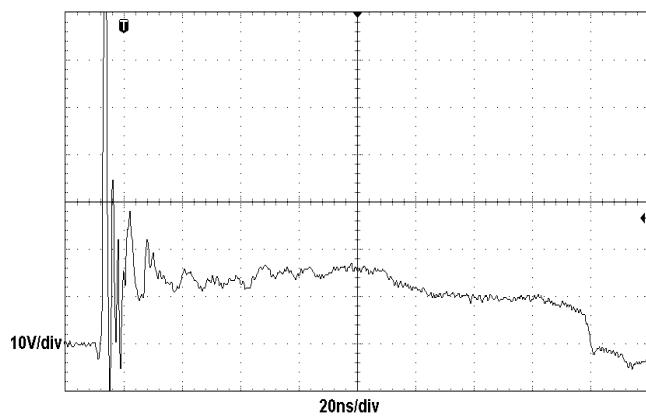
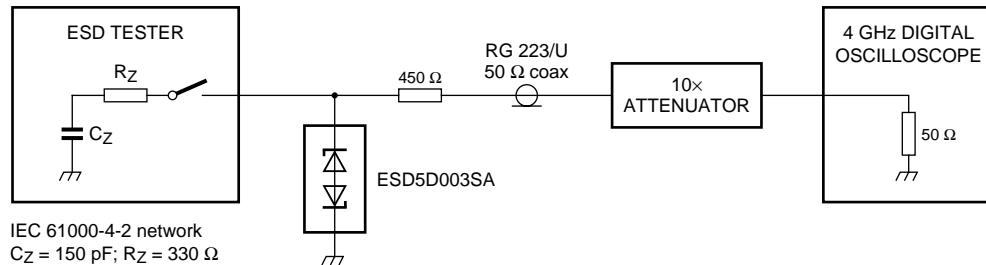
Typical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

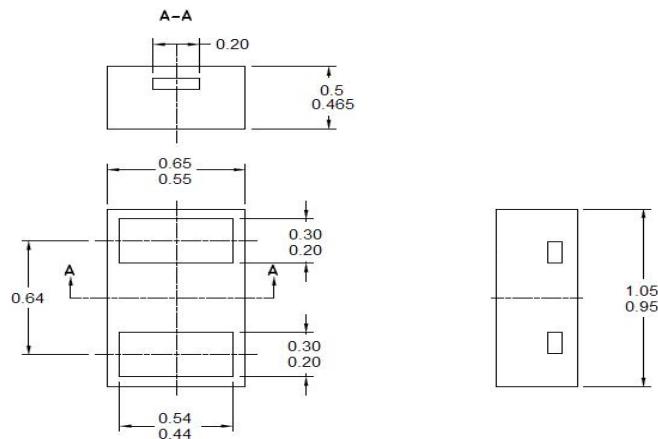
Non-repetitive peak pulse power vs. Pulse time



Power derating vs. Ambient temperature

ESD clamping test setup and waveforms



Package outline dimensions**DIMENSION OUTLINE: Unit:mm****Recommended Mounting Pad Layout Unit:mm**